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				APPLICANT: Toshikazu MUKAIHARA et al			
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		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB	
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<i>DATA</i>		JP 10-154847 A	6-1998	Japan			X*
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<i>Doc</i>	A. KASUKAWA et al, "Extremely High Power 1.48 μ m GaInAsP/InP GRIN-SCH Strained MQW Lasers", <u>IEEE PHOTONICS TECHNOLOGY LETTERS</u> , Vol. 6, No. 1 pp. 4-6 (January 1994).						
<i>Doc</i>	P. GAVRILOVIC et al, "CW High Power Single-Lobed Far-Field Operation of Long-Cavity AlGaAs-GaAs Single-Quantum-Well Laser Diodes Grown by MOCVD, <u>Journal of Quantum Electronics</u> , Vol. 27, No. 7, pp. 1859-1862 (July 1991).						
EXAMINER: <i>Delma R. Flores Ruiz</i>				DATE CONSIDERED: <i>11/29/02</i>			
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